#### Film in tension

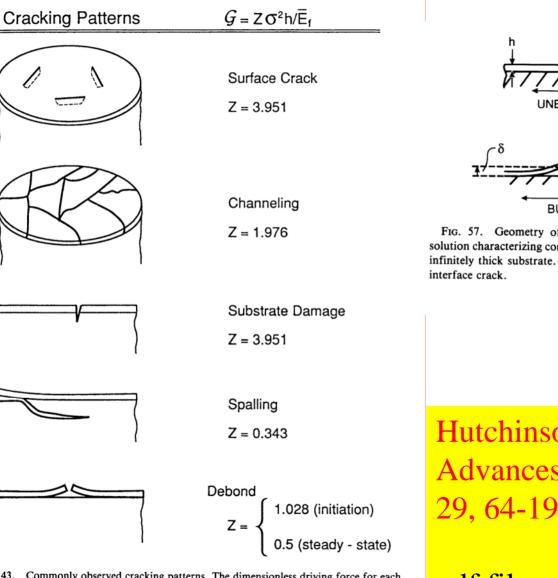


FIG. 43. Commonly observed cracking patterns. The dimensionless driving force for each pattern is listed, assuming that the film-substrate is elastically homogeneous, and the substrate is infinitely thick.

#### Film in compression

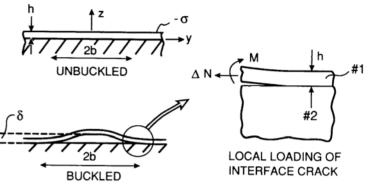


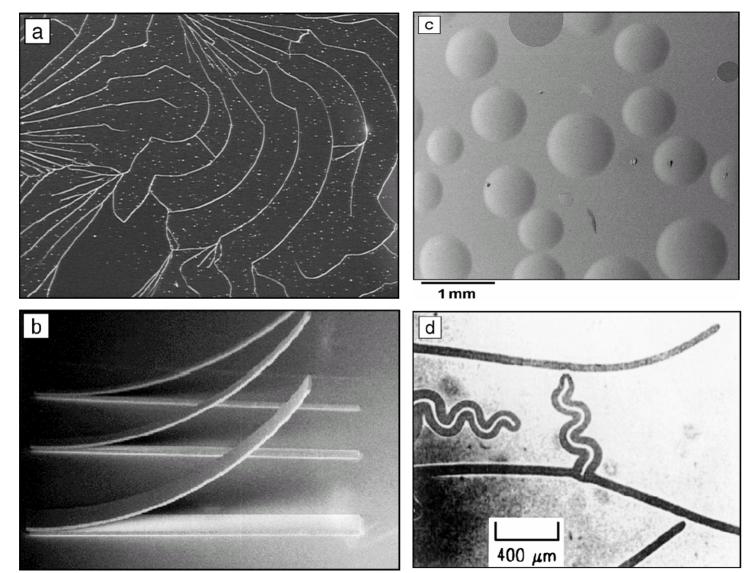
FIG. 57. Geometry of the one-dimensional blister, and conventions for the elasticity solution characterizing conditions near the tip of an interface crack between a thin film and an infinitely thick substrate. Top left: unbuckled; bottom left: buckled; right: local loading of interface crack.

Hutchinson, Suo Advances in Applied Mechanics 29, 64-192 (1992).

pdf file: www.deas.harvard.edu/suo

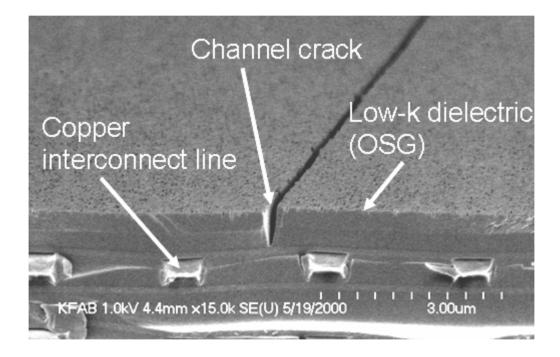
129

# Variety of Thin Film Fracture Patterns



Cook, Suo, MRS Bulletin, 27, 45 (2002) Courtesy J. Sturn (a), (c); Q. Ma (b); M.D. Thouless (d)

## A channel crack



#### T. Tsui (http://www.imechanica.org/node/248)

# The origin of stress in a film

- Deposition process (intrinsic stress)
- Mismatch due to lattice constant
- Mismatch in the coefficient of thermal expansion
- Bending

W.D. Nix, Mechanical Properties of Thin Films (http://imechanica.org/node/530)

# Stress in a thin film due to mismatch in the coefficients of thermal expansion

- •The film is very thin compared to the substrate (h << H).
- •The substrate is nearly stress free.
- •The film is in a state of equal biaxial stress,  $\sigma$ .
- •At T<sub>ref</sub>, the film is stress free.
- •The film deforms elastically as the temperature changes

$$\varepsilon_s = \alpha_s (T - T_{ref})$$
  $\varepsilon_f = \alpha_f (T - T_{ref}) + \frac{(1 - \nu_f)\sigma}{E_f}$ 

As the temperature changes, the substrate and the film remains bonded

$$\varepsilon_s = \varepsilon_f$$

$$\sigma = \frac{E_f}{(1 - \nu_f)} (\alpha_f - \alpha_s) (T_{ref} - T)$$

When  $\alpha_f > \alpha_s$ , upon cooling, the film is under tensile stress,  $\sigma > 0.5$ 

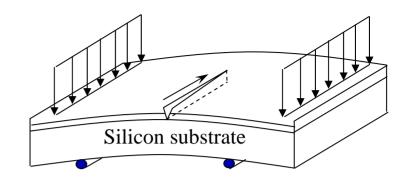
Stress in film due to bending

$$\frac{1}{R} = \frac{M}{\frac{E_s}{12\left(1 - v_s^2\right)}BH^3}$$

$$\varepsilon = \frac{H/2}{R}$$

$$\sigma = \frac{E_f}{1 - v_f^2} \varepsilon$$

$$\sigma = \frac{6E_f \left(1 - v_s^2\right)M}{E_s \left(1 - v_f^2\right)BH^2}$$



- M = applied moment
- B = width of the beam
- H = thickness of the substrate
- R = radius of curvature
- $\varepsilon = strain$  in the film
- $\sigma$  = stress in the film

Measure residual stress using wafer curvature

Line tension 
$$f = \int \sigma dz$$

Bending moment 
$$M = fBH/2$$

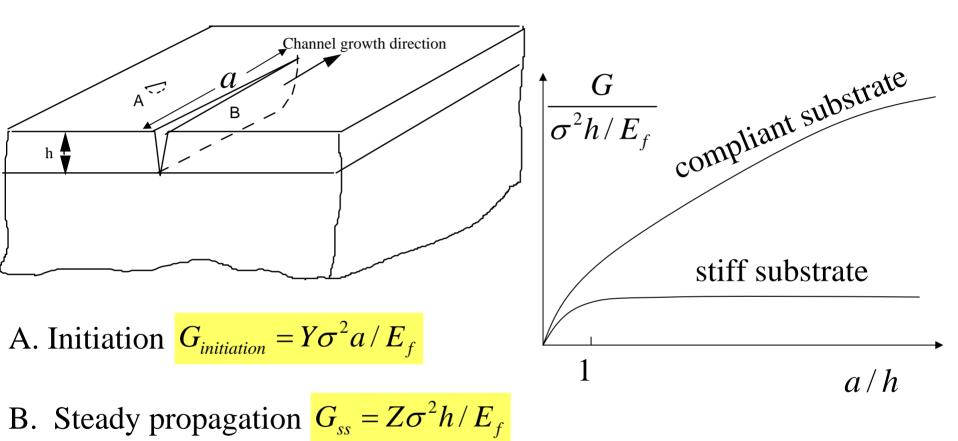
Radius of curvature

$$\frac{1}{R} = \frac{1 - v_s}{E_s} \frac{12M}{BH^3}$$

Stoney's formula

$$f = \left(\frac{E_s}{1 - v_s}\right) \frac{H^2}{6R}$$

#### Channel crack: Initiation vs. steady propagation



When the substrate is compliant, steady state is attained at a large a/h and a large energy release rate.

Steady-state energy release rate of a channel crack

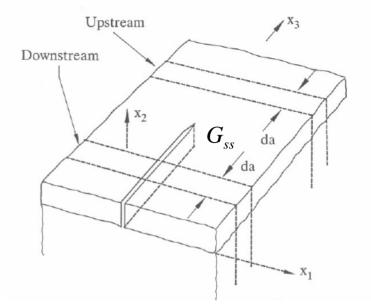
Reduction in elastic energy for the crack to advance a unit distance

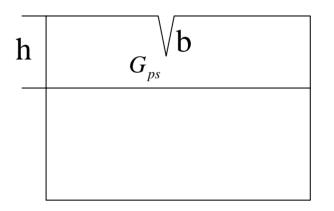
 $U = SE_{upstream} - SE_{downstream}$ 

 $U = \int_{0}^{h} G_{ps}(b)$ 

Steady-state energy release rate

$$hG_{ss} = U \qquad G_{ss} = \frac{1}{h} \int_{0}^{h} G_{ps}(b) db$$





Example: film and substrate have similar elastic modulus

$$G_{ps}(b) = \frac{1 - v^2}{E} (1.1215)^2 \pi b \sigma^2 \qquad G_{ss} = 2 \frac{(1 - v^2)}{E} h \sigma^2$$

Steady-state energy release rate of a channel crack

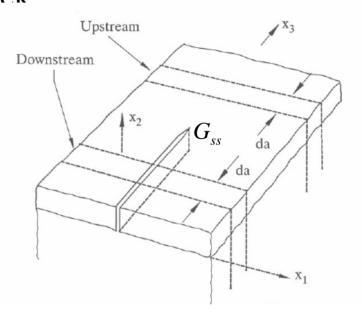
Reduction in elastic energy for the crack to advance a unit distance  $U = SE_{upstream} - SE_{downstream}$ 

$$U = \frac{1}{2} \int_{0}^{h} \delta(z) \sigma(z) dz$$

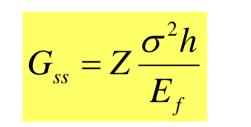
 $\delta(z)$  Crack opening downstream  $\sigma(z)$  Stress upstream

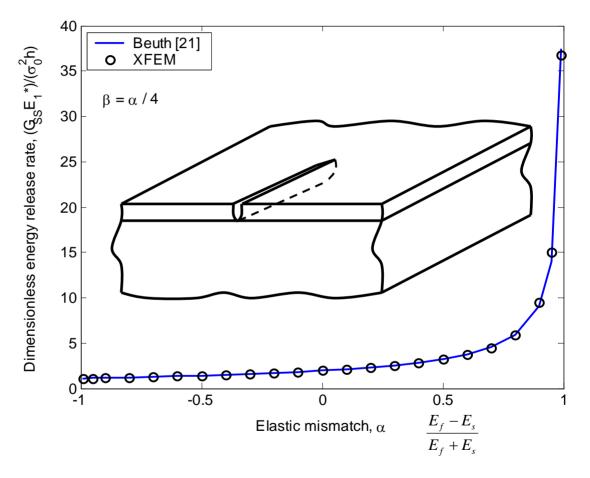
 $hG_{ss} = U$ 

$$G_{ss} = \frac{1}{2h} \int_{0}^{h} \delta(z) \sigma(z) dz$$



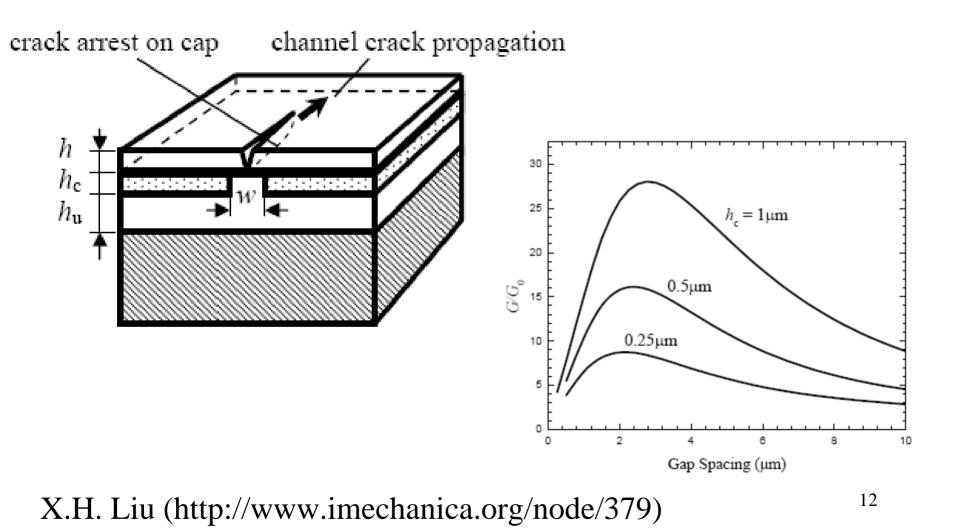
# Driving force for steady propagation



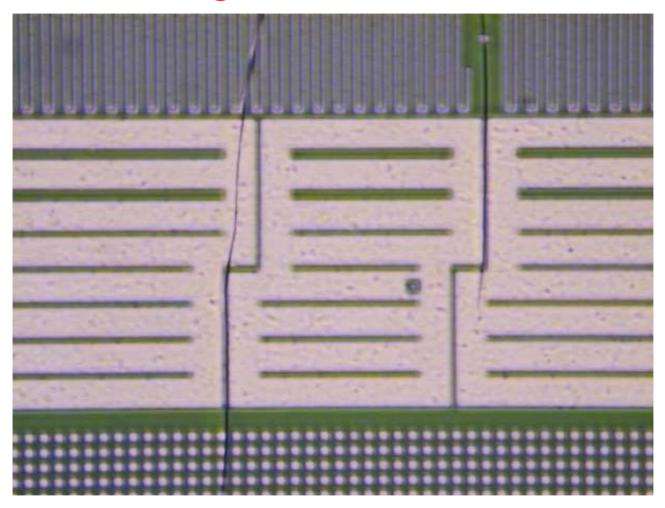


An advantage of being nano: thin films can sustain large stains. e.g., 7 nm silica film can sustain strains of  $\sim 5\%$ .

## Channel crack in patterned structure



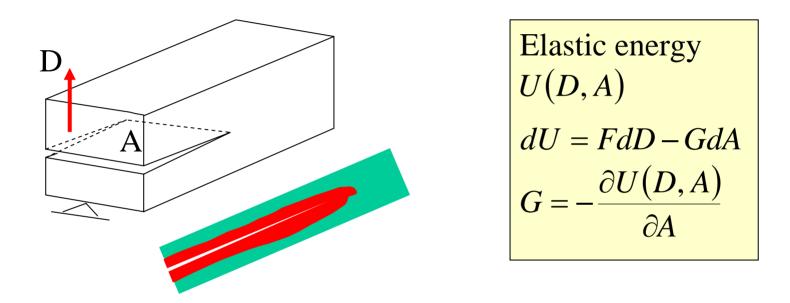
## Cracking in low k dielectrics



Also see a thread of discussion at http://www.imechanica.org/node/165

# Crack driving force, G

Generalized coordinates: D = displacement, A = crack area



#### Work supply = elastic energy + excess

In *steady state*, the excess is proportional to crack area,  $\Gamma A$ 

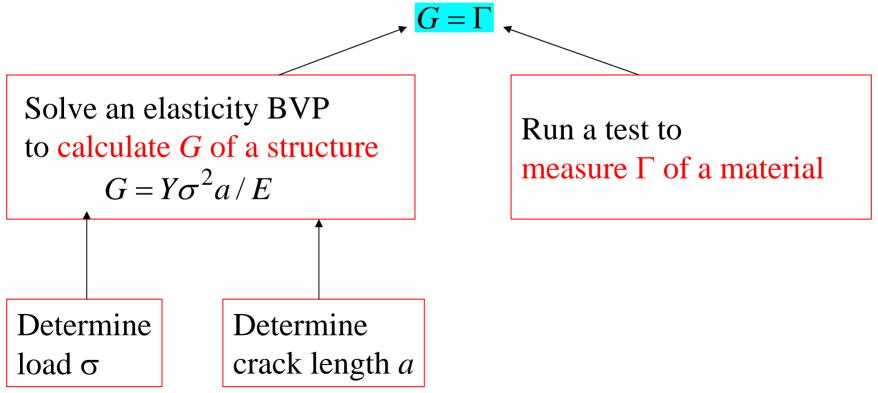
$$FdD = dU + \Gamma dA$$

$$G = \Gamma$$

## Fracture mechanics as a division of labor

George Rankin Irwin (1907-1998)

Crack driving force, G. Crack resistance,  $\Gamma$ 

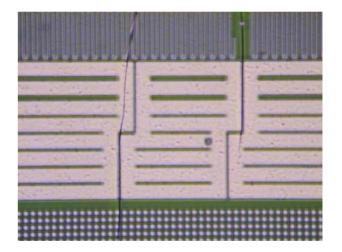


## Small structures: a new economy

Calculating G is prohibitively expensive

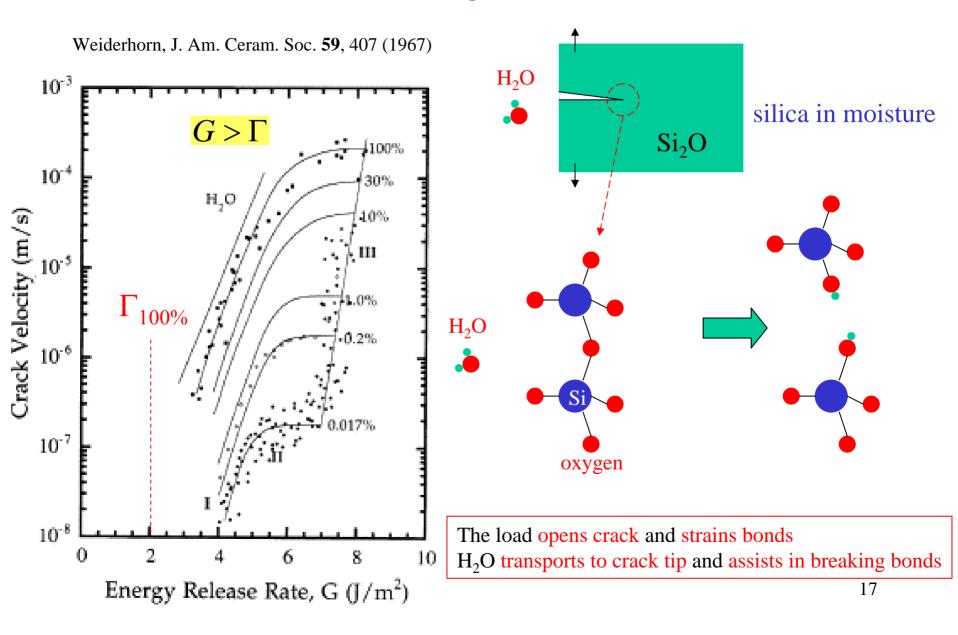
•3D architecture
•uncertain flaws
•uncertain residual stress field
•uncertain material properties

• Massive testing is cheap.



### A new division of labor: run test to measure G!

#### Moisture-assisted crack growth: the V-G function



## A method to measure G

V-G function is specific to material and environment, and remains the same when the material is integrated into a structure.

Use a simple structure to measure V-G function.

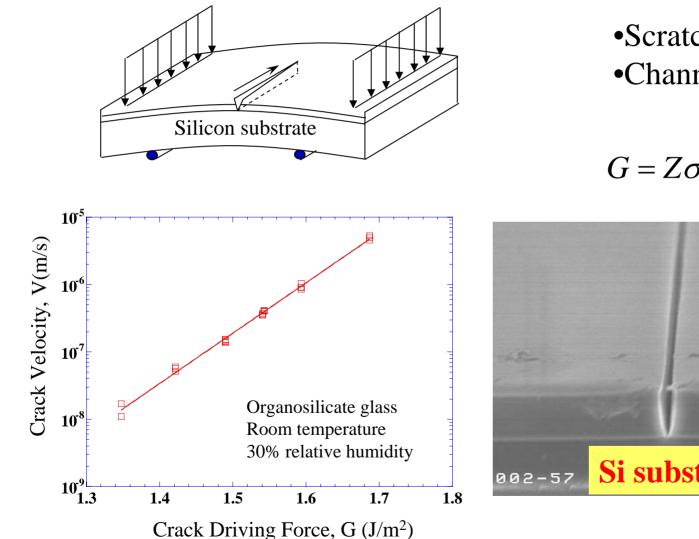
In a complex structure, an observed V gives a reading of G.

... in a way analogous to measuring temperature

Thermometer  $\longrightarrow$  G-meter

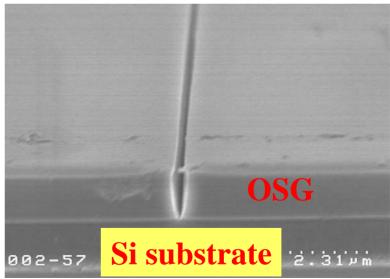
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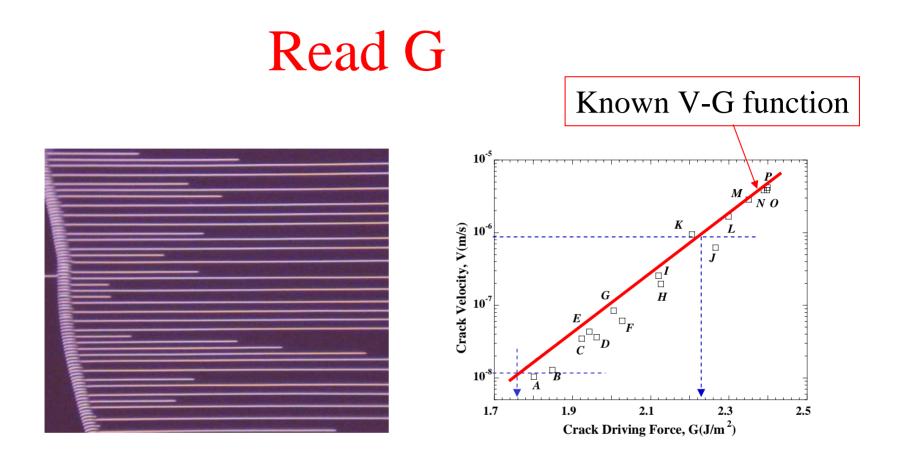
### Measure the V-G function



•Scratch and bend •Channel crack

$$G = Z\sigma^2 h / \overline{E}$$





$$G = \frac{\sigma^2 Zh}{\overline{E}} \left( \tanh\left(\frac{S_1}{2Zh}\right) + \tanh\left(\frac{S_2}{2Zh}\right) - \tanh\left(\frac{S_1 + S_2}{2Zh}\right) \right)$$
  
Xia, Hutchinson, J. Mech. Phys. Solids **48**, 1107 (2000).

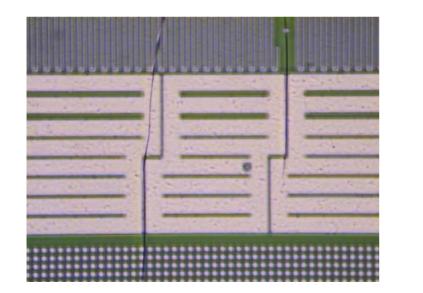
# Measure crack driving force due to residual stress field, G<sub>R</sub>

At G<sub>R</sub>, the crack velocity is too low to be observed.

Bend structure, observe crack velocity, and read G.
Extrapolate the data to obtain G<sub>R</sub>

Κ

 $K_R$ 



$$G = K^2 / \overline{E}$$
$$K = K_R + BF$$

To be immortal,  $G_R < \Gamma$